EDI8M4512C
45/55/70
Module

The future . . . today.

ADVANCE INFORMATION

512Kx4 SRAM CMOS, High Speed Module

The EDI8M4512C is a Two Megabit (512Kx4-bit) High Speed Static RAM Module with four bi-directional input/output lines. The module is constructed of eight 64Kx4 Static RAMs in leadless chip carriers surface mounted on a multi-layered ceramic substrate.

All inputs and outputs of the EDI8M4512C are TTL-compatible and operate from a single 5V supply. Fully asynchronous circuitry is used requiring no clocks or refreshing for operation and providing equal access and cycle times for ease of use.

EDI military grade modules are constructed with semiconductor components which are 100% processed to the test methods of MIL-STD-883 Class B, making them ideally suited to applications demanding the highest level of performance and reliability.

Features

512Kx4 bit, Two Megabit Density CMOS Static Random Access Memory Module
- Fast Access Times of 45, 55, and 70ns
- Low power consumption
- Common I/O lines
- TTL-compatible inputs and outputs

32 pin DIP, 600 mil centers
Single +5V (±10%) Supply Operation

Pin Names

AØ-A18	Address Inputs
$\overline{E}$	Chip Enables
$\overline{W}$	Write Enable
DQØ-DQ3	Data Input/Output
VCC	Power (+5V±10%)
VSS	Ground

Pin Configuration and Block Diagram



